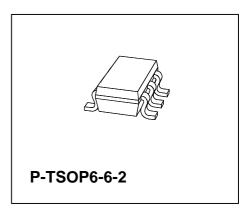


# Low Power Hall Switch

TLE 4917

# Features

- Micro power design
- 2.4 V to 5.5 V battery operation
- High sensitivity and high stability of the magnetic switching points
- High resistance to mechanical stress
- Digital output signal
- Switching for both poles of a magnet (omnipolar)
- Programming pin for the switching direction of the output



## **Functional Description**

The TLE 4917 is an Integrated Hall-Effect Sensor designed specifically to meet the requirements of low-power devices. eg as an On/Off switch in Cellular Flip-Phones, with battery operating voltages of 2.4V - 5.5V.

Precise magnetic switching points and high temperature stability are achieved through the unique design of the internal circuit.

An onboard clock scheme is used to reduce the average operating current of the IC.

During the operate phase the IC compares the actual magnetic field detected with the internally compensated switching points. The output Q is switched at the end of each operating phase.

During the Stand-by phase the output stage is latched and the current consumtion of the device reduced to some  $\mu A$ .

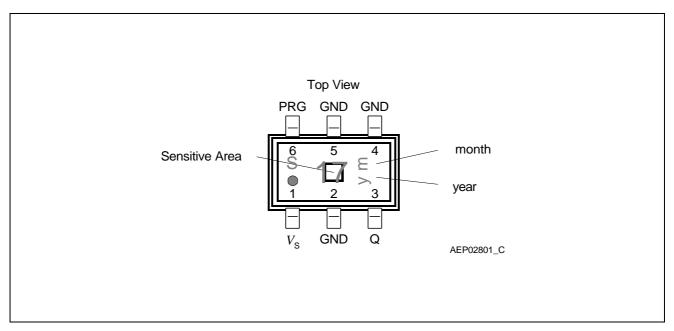
The IC switching behaviour is omnipolar, i.e. it can be switched on with either the North or South pole of a magnet.

The PRG pin can be connected to V<sub>S</sub> which holds the output V<sub>Q</sub> at a High level for B=0mT; conversely the output V<sub>Q</sub> can be inverted by connecting the PRG pin to Gnd, which will hold the output V<sub>Q</sub> at a Low level for B=0mT. In this later case the presence of an adequate magnetic field will cause the output V<sub>Q</sub> to switch to a High level ( ie off state ).

Туре	Marking	Ordering Code	Package
TLE 4917	17s	Q62705K 605	P-TSOP6-6-2



# **Pin Configuration** (top view)



# Figure 1

# **Pin Definitions and Functions**

Pin	Symbol	Function
1	$V_{S}$	Supply Voltage
2	GND	Ground
3	Q	Open Drain Input
4	GND	Ground
5	GND	Ground
6	PRG	Programming Input



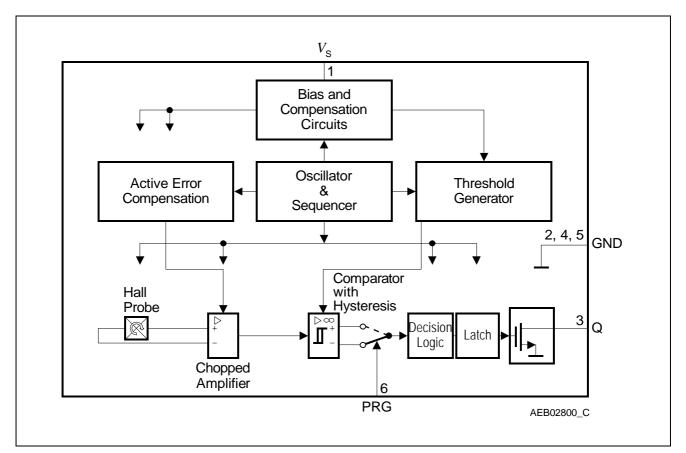


Figure 2 Block Diagram

## **Circuit Description**

The Low Power Hall IC Switch comprises a Hall probe, bias generator, compensation circuits, oscillator, output latch and an n-channel open drain output transistor.

The bias generator provides currents for the Hall probe and the active circuits. Compensation circuits stabilize the temperature behavior and reduce technology variations.

The Active Error Compensation rejects offsets in signal stages and the influence of mechanical stress to the Hall probe caused by moulding and soldering processes and other thermal stresses in the package. This chopper technique together with the threshold generator and the comparator ensures high accurate magnetic switching points.

Very low power consumption is achieved with a timing scheme controlled by an oscillator and a sequencer. This circuitry activates the sensor for 50  $\mu$ s (typical operating time) sets the output state after sequential questioning of the switchpoints and latches it with the beginning of the following standby phase (typ. 130 ms). In the standby phase the average current is reduced to typical 3.5  $\mu$ A. Because of the long standby time compared to the operating time the overall averaged current is only slightly higher than the standby current.

By connecting the programming pin to GND (normal to  $V_s$ ) the Output State can be inverted to further reduce the current consumption in applications where a high magnetic field is the



normal state. In that case the output Q is off at high magnetic fields and no current is flowing in the open drain transistor.

The output transistor can sink up to 1 mA with a maximal saturation voltage  $U_{QSAT}$ .

### Absolute Maximum Ratings

Parameter	Symbol Limit Val		Values	Unit	Notes
		min.	max.		
Supply Voltage	Vs	- 0.3	5.5	V	
Supply Current	Is	- 1	2.5	mA	
Output Voltage	$V_{Q}$	- 0.3	5.5	V	
Output Current	IQ	- 1	2	mA	
Programming Pin Voltage	$V_{PRG}$	- 0.3	5.5 <sup>1)</sup>	V	
Junction temperature	Ti	- 40	150	°C	
Storage temperature	T <sub>S</sub>	- 40	150	°C	
Magnetic Flux Density	В	-	unlimited	mT	
Thermal Resistance P-TSOP6-6-2	$R_{ m th~JA}$	-	35	K/W	

 $^{1)}V_{\rm PRG}$  must not exceed Vs by more than 0.3V

Note: Stresses above those listed here may cause permanent damage to the device. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

### **ESD** Protection

Human Body Model (HBM) tests according to: EOS/ESD Association Standard S5.1-1993 and Mil. Std. 883D method 3015.7

Parameter	Symbol	Limi	t Values	Unit	Notes
		Min.	max.		
ESD Voltage	$U_{ESD}$	± 2		kV	$R = 1.5 \Omega$ ,
					<i>C</i> = 100 pF;
					<i>T</i> = 25 °C



## **Operating Range**

Parameter	Symbol	Limit Values			Unit	Notes	
		Min.	typ.	max.			
Supply voltage	Vs	2.4	2.7	5.5	V	1)	
Output voltage	$V_{Q}$	- 0.3	2.7	5.5	V		
Programming Pin Voltage	V <sub>PRG</sub>	- 0.3	0	0.3	V	Inverted output state	
		V <sub>S</sub> – 0.3	Vs	V <sub>S</sub> + 0.3		Standard output state	
Ambient Temperature	T <sub>A</sub>	- 40	25	85	°C		

 $^{\rm 1)}$  A Ceramic Bypass Capacitor of 10 nF at  $V_{\rm S}$  to GND is highly recommended.

## **AC/DC Characteristics**

Parameter	Symbol	Limit Values			Unit	Notes
		Min.	typ.	Max.		
Averaged Supply Current	I <sub>SAVG</sub>	1	4	20	μA	
Averaged Supply	ISOPAVG	0.5	1.1	2.5	mA	
Current						
during Operating Time						
Transient Peak Supply	I <sub>SOPT</sub>	-	-	2.5	mA	<i>t</i> < 100 ns
Current						
during Operating Time						
Supply Current	I <sub>SSTB</sub>	1	3.5	20	μA	
during Standby Time						
Output Saturation Voltage	$U_{QSAT}$	-	0.13	0.4	V	$I_Q = 1 \text{ mA}$
Output Leakage Current	I <sub>QLEAK</sub>	-	0.01	1	μA	
Output Rise Time	t <sub>r</sub>	-	0.3	1	μs	$R_{\rm L} = 2.7 \ {\rm k}\Omega;$
						$C_{\rm L} = 10 \ {\rm pF}$
Output Fall Time	<i>t</i> <sub>f</sub>	-	0.1	1	μs	$R_{\rm L} = 2.7 \ {\rm k}\Omega;$
						$C_{\rm L} = 10  \rm pF$
Operating Time	t <sub>op</sub>	15	50	93 <sup>1)</sup>	μs	2)
Standby Time	t <sub>stb</sub>	-	130	240 <sup>3)</sup>	ms	
Duty Cycle	t <sub>op</sub> / t <sub>stb</sub>	-	0.039	-	%	
Start-up Time of IC	t <sub>stu</sub>	-	6	12	μs	4)

<sup>1)</sup> for V<sub>S</sub>=3.5V the max. operating time  $t_{op max} = 85\mu s$ <sup>2)</sup> includes the Start-up Time  $t_{stu}$ 

<sup>3)</sup> for V<sub>S</sub>=3.5V the max. Standby Time  $t_{\rm stb\ max}$  = 220ms <sup>4)</sup> initial power on time



## Magnetic Characteristics

Parameter	Symbol	mbol Limit Values		Unit	Notes	
		min.	typ.	max.		
Operate Points	B <sub>OPS</sub>	3.5	5	7	mT	1)
	BOPN	-7	- 5	- 3.5	mT	
Release Points	B <sub>RPS</sub>	2.2	4	6	mT	1)
	B <sub>RPN</sub>	- 6	- 4	- 2.2	mT	
Hysteresis	B <sub>HY</sub>	0.2	1	2	mT	

<sup>1)</sup> Positive magnetic fields are related to the approach of a magnetic south pole to the branded side of package

Note: The listed AC/DC and magnetic characteristics are ensured over the operating range of the integrated circuit. Typical characteristics specify mean values expected over the production spread. If not other specified, typical characteristics apply at  $T_j = 25$  °C and  $V_S = 2.7$  V.



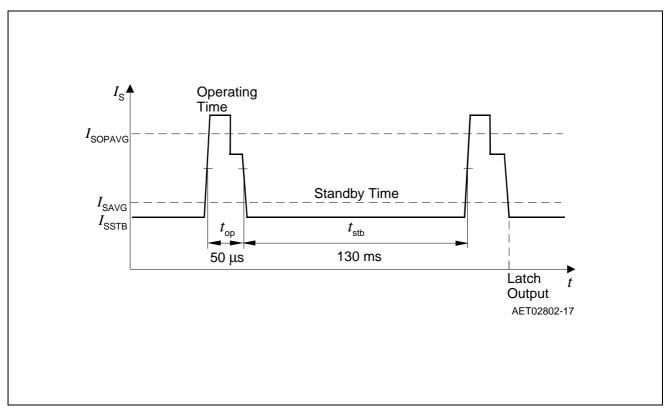


Figure 3 Timing Diagram

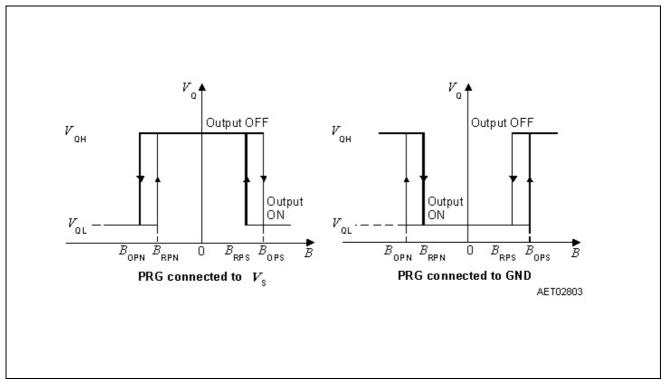
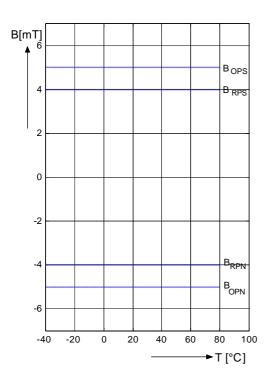


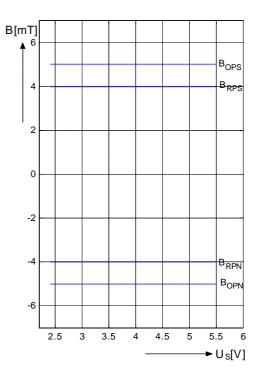
Figure 4 Programming of Output with the PRG Pin



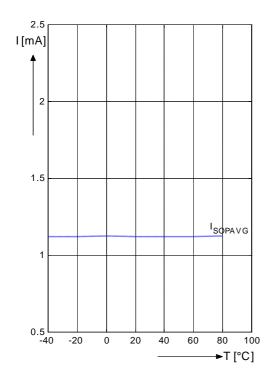
# Magnetic Switching Points versus Temperature (V<sub>s</sub>=2.7V)



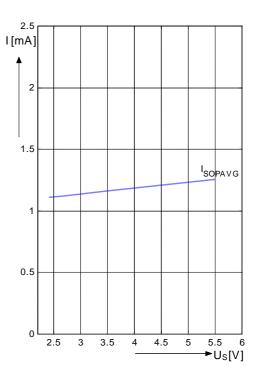
# Magnetic Switching Points versus Supply Voltage U<sub>s</sub> (T<sub>a</sub>=20°C)



# Supply current I<sub>SOPAVG</sub> during Operating Time versus Temperature (V<sub>s</sub>=2.7V)

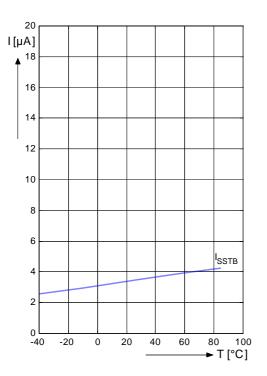


Supply current I<sub>SOPAVG</sub> during Operating Time versus Supply Voltage U<sub>s</sub> (T<sub>a</sub>=20°C)

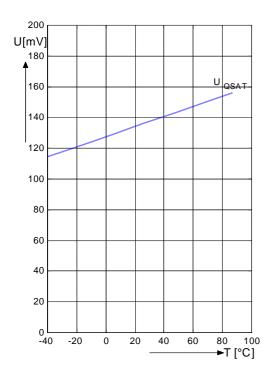




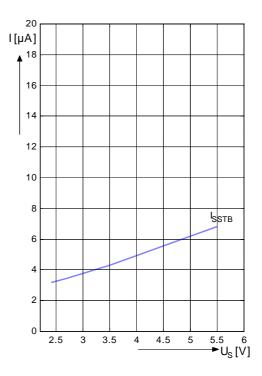
# Supply current I<sub>SSTB</sub> during Standby Time versus Temperature (V<sub>s</sub>=2.7V)



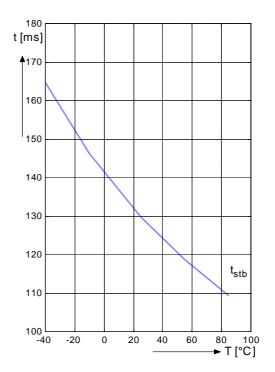
# Output Saturation voltage $U_{QSAT}$ versus Temperature ( $I_Q=1mA$ )



# Supply current I<sub>SSTB</sub> during Standby Time versus Supply Voltage U<sub>s</sub> (T<sub>a</sub>=20°C)



# Standby Time $t_{stb}$ versus Temperature (V<sub>s</sub> = 2.7V)





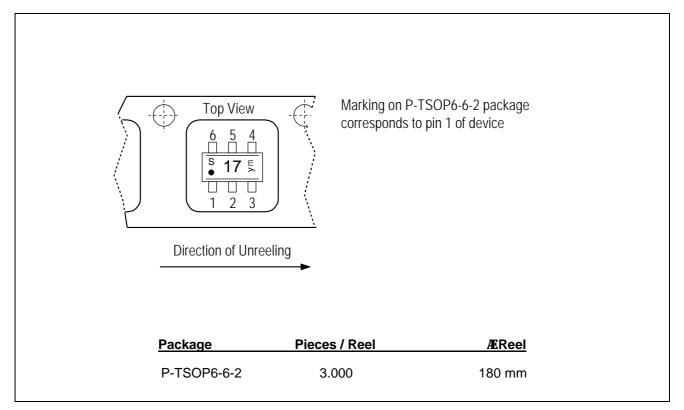


Figure 5 Marking and Tape Loading Orientation

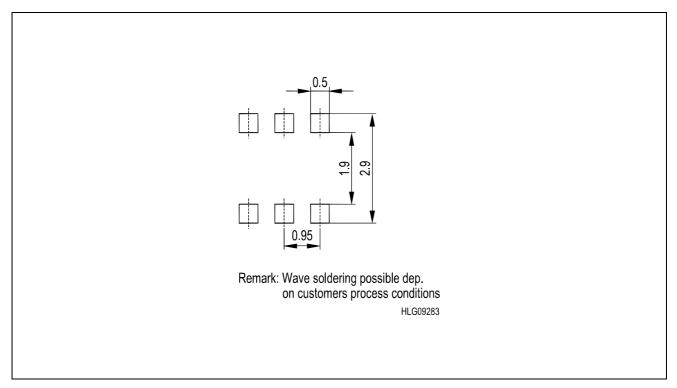
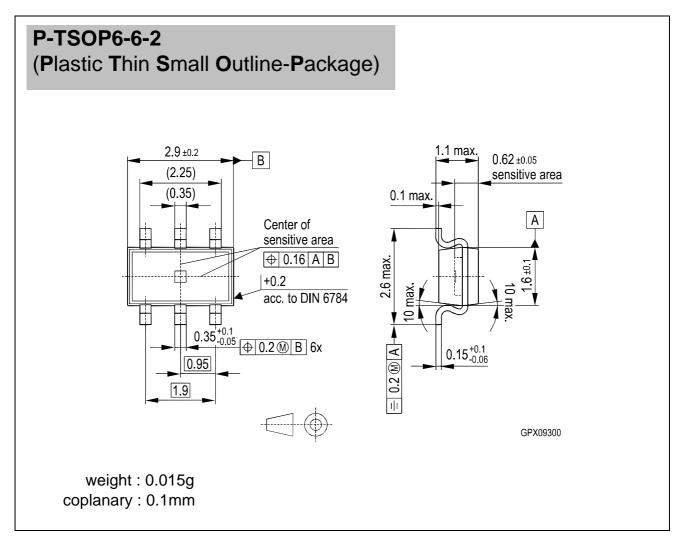


Figure 6 Foot Print Reflow Soldering



## Package Dimensions

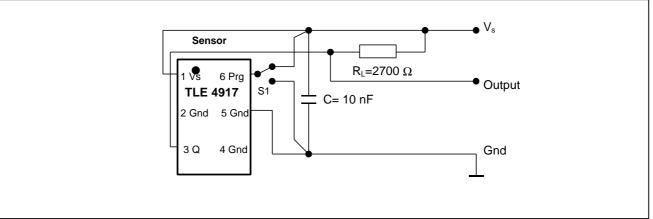


### Sorts of Packing

Package outlines for tubes, trays etc. are contained in our Data Book "Package Information".

SMD = Surface Mounted Device





# Information about the application circuit of the TLE 4917

## **Application circuit TLE 4917**

The minimum value for the pull up resistor can be calculated with the power supply voltage Vs, the maximum current IQmax and the minimum output saturation voltage UQSAT.

Example:

for Vs = 3 V: R<sub>Lmin</sub> = (Vs - UQSATmin)/IQmax = (3 V - 0,1 V)/0,002 A = 1435  $\Omega$ 

Larger values for  $R_L$  will reduce the current  $I_Q$  and therefore the power consumption. If the resistor RL is very large (>100 kOhm) a capacitor (app. 10pF) between Output and Gnd pin could be useful if capacitive coupled noise occurs.

The load at the output Q should have a large input resistance to reduce the current trough  $R_L$  and the power consumption.

The TLE 4917 has 3 ground pins. From a mechanical point of view all ground pins should be connected to ground. Shortest wires should be used to avoid ground loops.

If there is a need to reduce the number of used ground-pins any ground-pin combination may me used. Furthermore it is possible using only one ground-pin at the application, all pins are equivalent.

The capacitor C is highly recommended to reduce noise on the power supply voltage and it will improve the EMI/EMC performance.

Furthermore it decreases the transient peak supply current during operation time. The IC toggles between low and high current consumption. This behaviour might produce additional noise at the power supply. The capacitor will reduce this noise.

Furthermore this capacitor is used to supply the sensor if microbreaks were (short loss of supply voltage) to occur.

Shortest connection wires between IC and capacitor should be used to avoid noise.

The switch S1 shows the programming feature of the output.

Example:

If the PRG-pin is connected to Vs the IC will hold the output Q at a high voltage level for B= 0 mT in this circuit. A magnetic field larger than the operating point will switch the output to low level. In typical applications the PRG-pin is connected directly to Vs or to Gnd depending on the technical needs. Avoid using a floating PRG-pin.



TLE 4917	
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